

Light-emitting diode



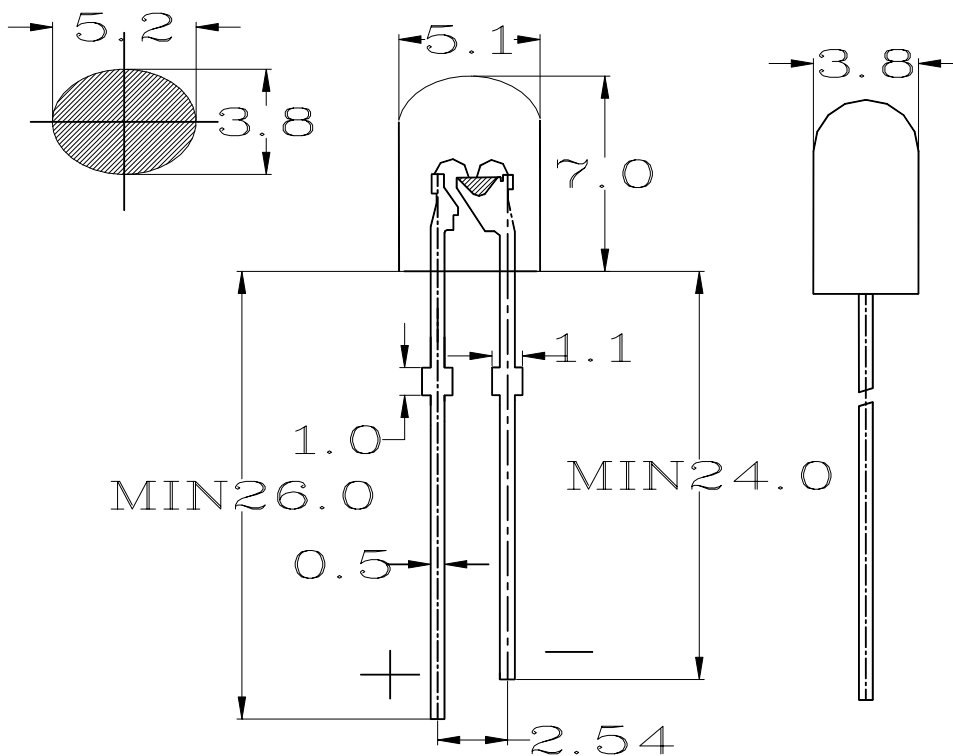
PartNumber: RL51N-GB714D/S1

Features

- 1.Low power consumption.
- 2.High efficiency.
- 3.Versatile mounting on p.c board or panel.
- 4.I.C compatible/ low current requirement.

Package Dimensions

Unit □mm



Selec

NOTE: TOLERANCE ± 0.2 mm

Part Number	Lens color	Chip		
		Material	Emitted color	λ_p (nm)
RL51N-GB714D/S1	Diffuse	InGaN	Green	520

Light-emitting diode



TECHNICAL SPECIFICATION

Part Number:RL51N-GB714D/S1

Parameter	Symbol	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Forward Voltage	VF	3.0	3.4	3.8	V	If=20mA
Peak Wavelength	λ_p	515	520		nm	
Reverse Current	IR			40	μ A	VR=5V
Power dissipation	Pd			100	mW	
Luminous Intensity	IV	1600	1800		mcd	If=20mA
Peak Forward Current	If(Peak)			100	mA	
Recommend Forward Current	If(Rec)		20		mA	
Full Viewing Angle	2 θ 1/2		100		deg	If=20mA

NOTE:

1.Luminous intensity is measured with a light sensor and fillister combination that approximates the CIE eye-response curve Tester: EG&G DR-2550.

2.IV classification code is marked on each packing bag. The IV base on line-on's bin classification. The IV guarantee should be add \pm 15%

3.Absolute maximum ratings: (Ta=25 \square)

4.Operating temperature : -40 \square TO 80 \square

5.Lead soldering: 260 \square for 5 seconds